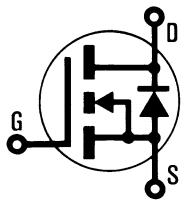
INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS IRFJ320 IRFJ321 IRFJ322 IRFJ323

N-CHANNEL POWER MOSFETs



400 Volt, 1.8 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, freedom from second breakdown, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

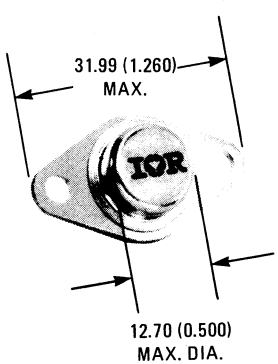
Features:

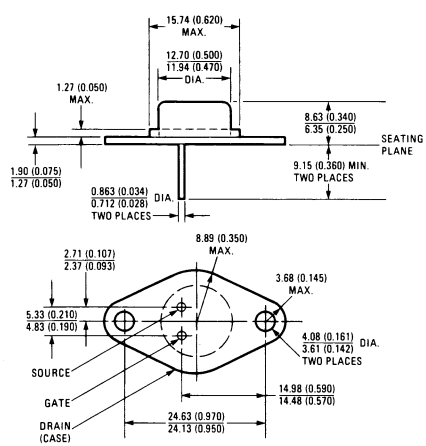
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ320	400V	1.8Ω	3.0A
IRFJ321	350V	1.8Ω	3.0A
IRFJ322	400V	2.5Ω	2.5A
IRFJ323	350V	2.5Ω	2.5A

CASE STYLE AND DIMENSIONS





Conforms to JEDEC Case Style TO-213AA (TO-66)
Dimensions in Millimeters and (Inches)

IRFJ320, IRFJ321, IRFJ322, IRFJ323 Devices

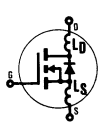
Absolute Maximum Ratings

Parameter		IRFJ320	IRFJ321	IRFJ322	IRFJ323	Units
V_{DS}	Drain - Source Voltage ①	400	350	400	350	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 kΩ) ①	400	350	400	350	V
I_D @ T_C = 25°C	Continuous Drain Current	3.0	3.0	2.5	2.5	A
I_D @ T_C = 100°C	Continuous Drain Current	2.0	2.0	1.5	1.5	A
I_{DM}	Pulsed Drain Current ③	12	12	10	10	A
V_{GS}	Gate - Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	40 (See Fig. 14)				W
	Linear Derating Factor	0.32 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH				A
		12	12	10	10	
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFJ320 IRFJ322	400	–	–	V	V_{GS} = 0V
		IRFJ321 IRFJ323	350	–	–	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS}	Gate - Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V
I_{GSS}	Gate - Source Leakage Reverse	ALL	–	–	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFJ320 IRFJ321	3.0	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V
		IRFJ322 IRFJ323	2.5	–	–	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFJ320 IRFJ321	–	1.5	1.8	Ω	V_{GS} = 10V, I_D = 1.6A
		IRFJ322 IRFJ323	–	1.8	2.5	Ω	
g_{fs}	Forward Transconductance ②	ALL	1.0	2.0	–	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 1.6A
C_{iss}	Input Capacitance	ALL	–	450	600	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	–	100	200	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	–	20	40	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	20	40	ns	V_{DD} ≃ 0.5 BV_{DSS}, I_D = 1.6A, Z_o = 50Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	–	25	50	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	50	100	ns	
t_f	Fall Time	ALL	–	25	50	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	12	15	nC	V_{GS} = 10V, I_D = 4.0A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	–	6.0	–	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	–	6.0	–	nC	
L_D	Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die.
L_S	Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.

Modified MOSFET symbol showing the internal device inductances.



Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	3.1	K/W	
R_{thCS}	Case-to-Sink	ALL	–	0.2	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	50	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ320 IRFJ321	–	–	3.0	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier.
		IRFJ322 IRFJ323	–	–	2.5	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFJ320 IRFJ321	–	–	12	A	
		IRFJ322 IRFJ323	–	–	10	A	
V_{SD}	Diode Forward Voltage ②	IRFJ320 IRFJ321	–	–	1.6	V	T_C = 25°C, I_S = 2.8A, V_{GS} = 0V
		IRFJ322 IRFJ323	–	–	1.5	V	T_C = 25°C, I_S = 2.4A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	–	450	–	ns	T_J = 150°C, I_F = 2.8A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	–	3.1	–	μC	T_J = 150°C, I_F = 2.8A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

①T_J = 25°C to 150°C. ②Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

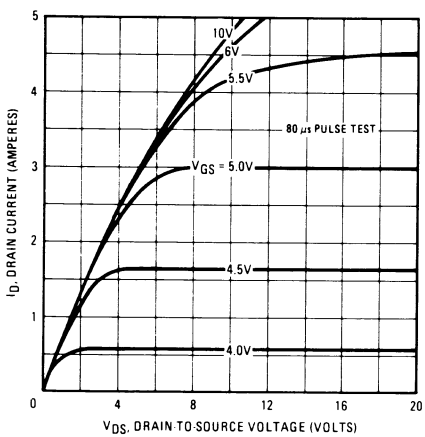


Fig. 1 – Typical Output Characteristics

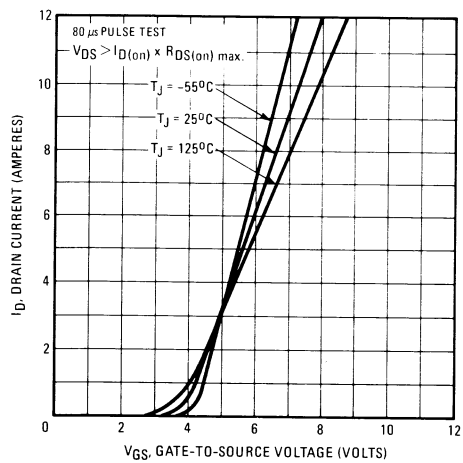


Fig. 2 – Typical Transfer Characteristics

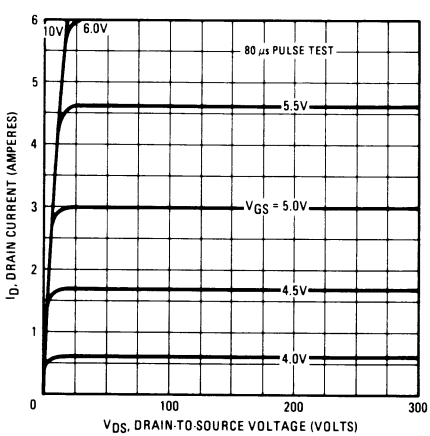


Fig. 3 – Typical Saturation Characteristics

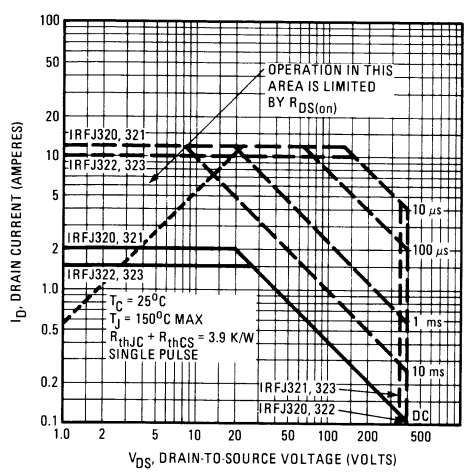


Fig. 4 – Maximum Safe Operating Area

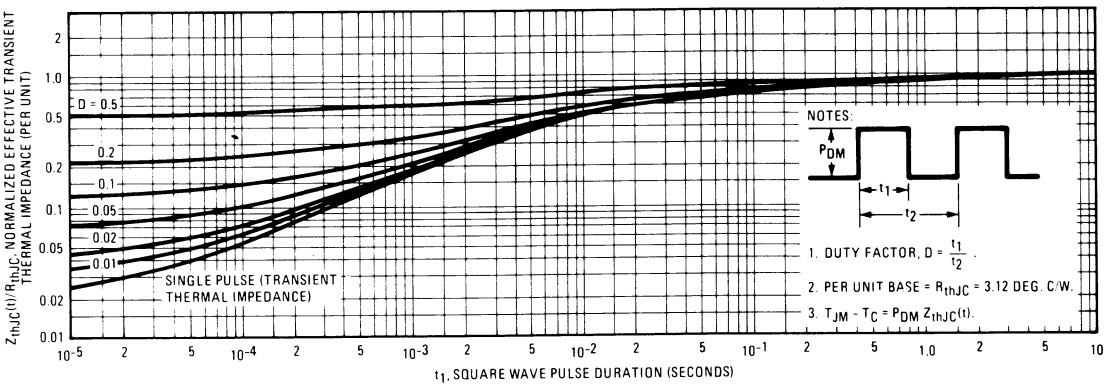


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

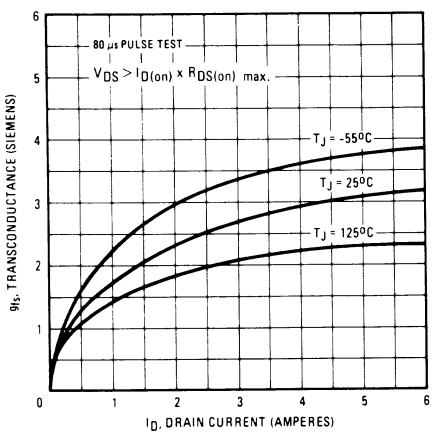


Fig. 6 — Typical Transconductance Vs. Drain Current

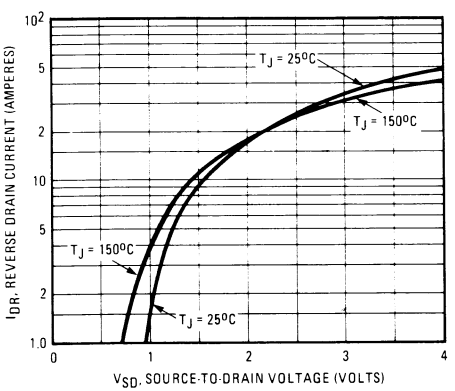


Fig. 7 — Typical Source-Drain Diode Forward Voltage

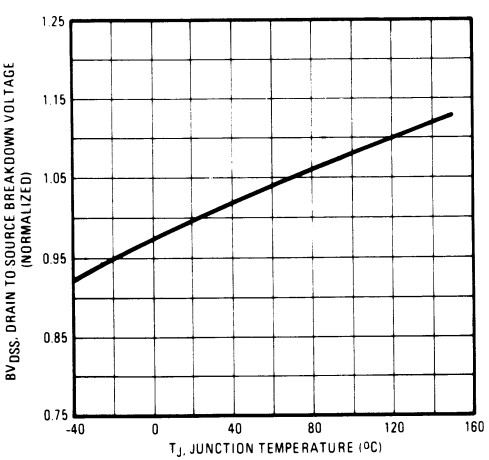


Fig. 8 — Breakdown Voltage Vs. Temperature

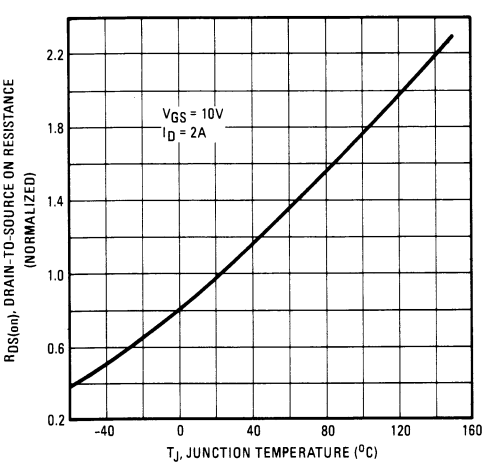


Fig. 9 — Normalized On-Resistance Vs. Temperature

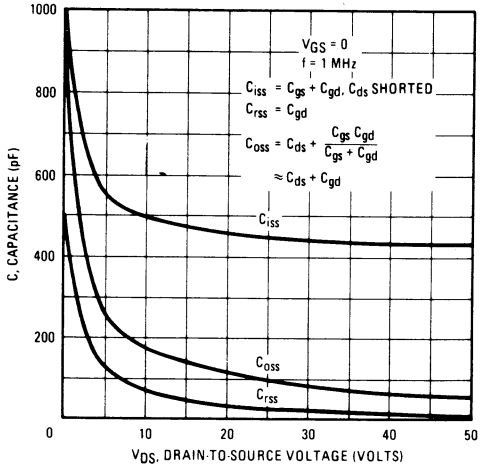


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

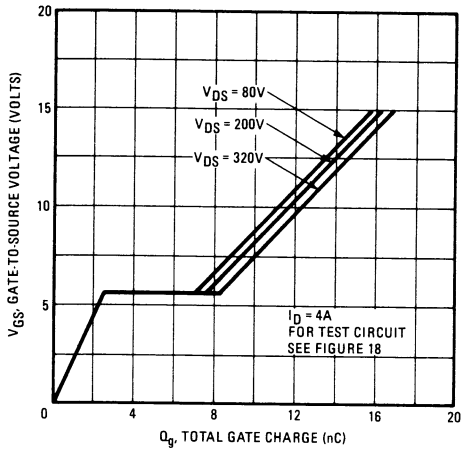


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

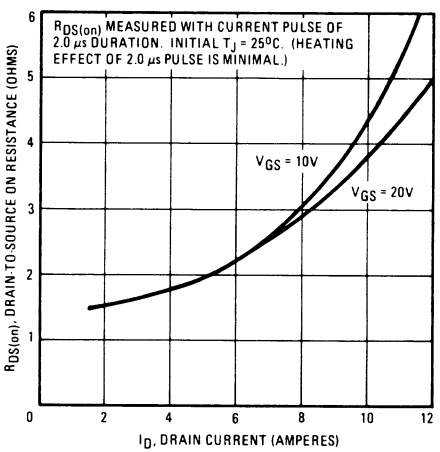


Fig. 12 — Typical On-Resistance Vs. Drain Current

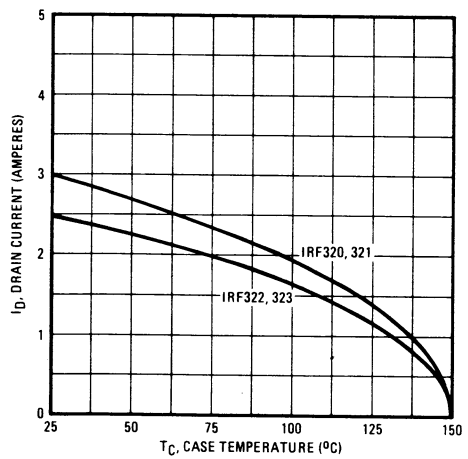


Fig. 13 — Maximum Drain Current Vs. Case Temperature

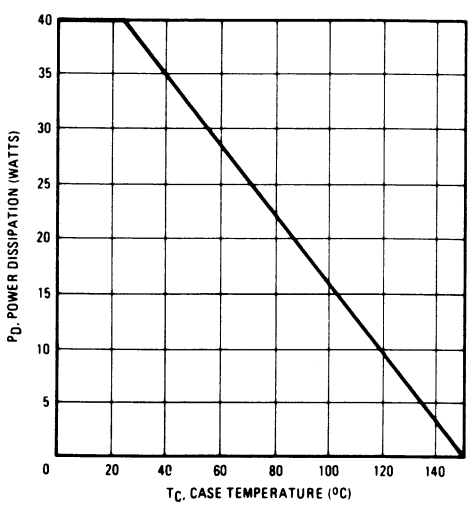


Fig. 14 — Power Vs. Temperature Derating Curve

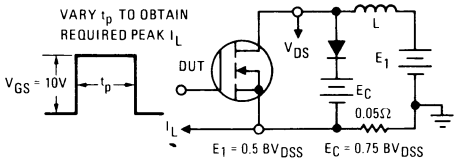


Fig. 15 – Clamped Inductive Test Circuit

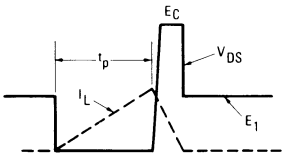


Fig. 16 – Clamped Inductive Waveforms

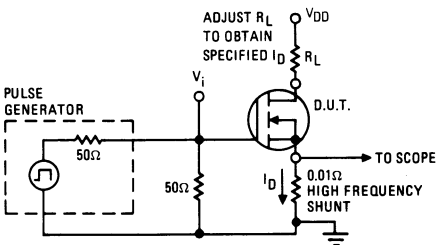


Fig. 17 – Switching Time Test Circuit

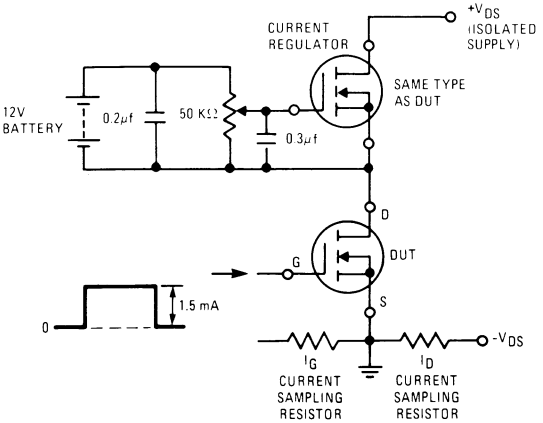


Fig. 18 – Gate Charge Test Circuit

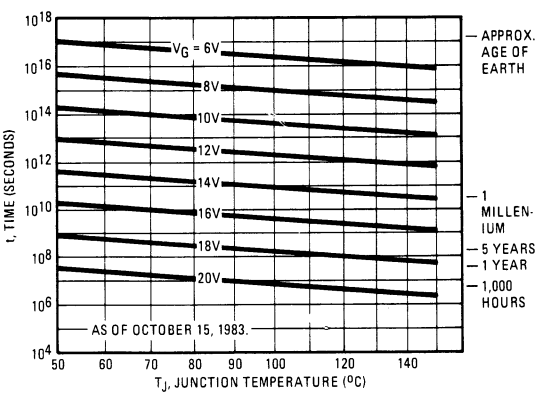


*Fig. 19 – Typical Time to Accumulated 1% Failure

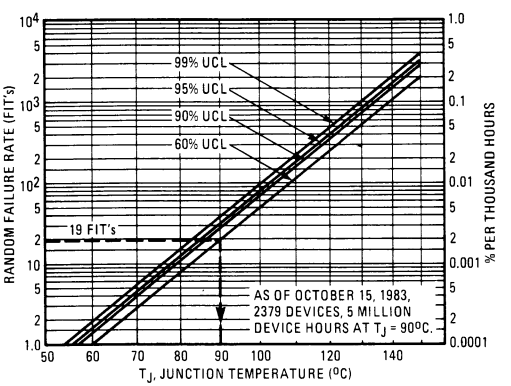


Fig. 20 – Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.

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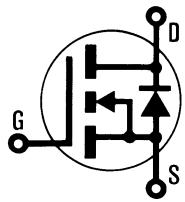
N-CHANNEL POWER MOSFETs



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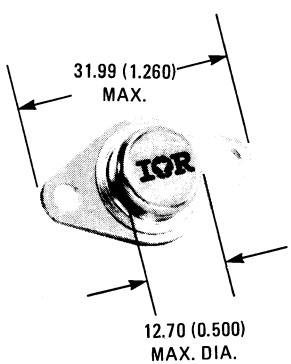
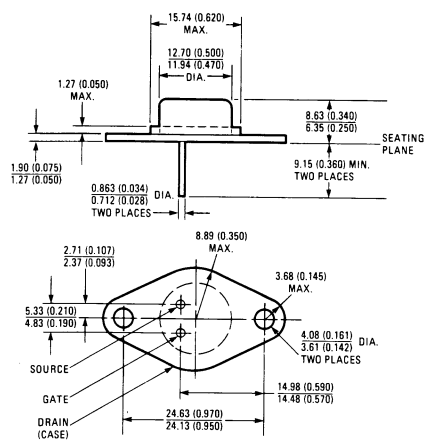
Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ330	400V	1.0Ω	4.5A
IRFJ331	350V	1.0Ω	4.5A
IRFJ332	400V	1.5Ω	4.0A
IRFJ333	350V	1.5Ω	4.0A

CASE STYLE AND DIMENSIONS





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Dimensions in Millimeters and (Inches)

IRFJ330, IRFJ331, IRFJ332, IRFJ333 Devices

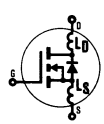
Absolute Maximum Ratings

Parameter		IRFJ330	IRFJ331	IRFJ332	IRFJ333	Units
V_{DS}	Drain - Source Voltage ①	400	350	400	350	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	400	350	400	350	V
I_D @ T_C = 25°C	Continuous Drain Current	4.5	4.5	4.0	4.0	A
I_D @ T_C = 100°C	Continuous Drain Current	3.0	3.0	2.5	2.5	A
I_{DM}	Pulsed Drain Current ③	18	18	15	15	A
V_{GS}	Gate - Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	50 (See Fig. 14)				W
	Linear Derating Factor	0.4 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 18	18	15	15	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFJ330 IRFJ332	400	–	–	V	V_{GS} = 0V
		IRFJ331 IRFJ333	350	–	–	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS}	Gate - Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V
I_{GSS}	Gate - Source Leakage Reverse	ALL	–	–	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFJ330 IRFJ331	4.5	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V
		IRFJ332 IRFJ333	4.0	–	–	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFJ330 IRFJ331	–	0.8	1.0	Ω	V_{GS} = 10V, I_D = 2.5A
		IRFJ332 IRFJ333	–	1.0	1.5	Ω	
g_{fs}	Forward Transconductance ②	ALL	3.0	4.0	–	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 2.5A
C_{iss}	Input Capacitance	ALL	–	700	900	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	–	150	300	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	–	40	80	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	–	30	ns	V_{DD} ≈ 175V, I_D = 2.5A, Z_o = 15Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	–	–	35	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	–	55	ns	
t_f	Fall Time	ALL	–	–	35	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	18	30	nC	V_{GS} = 10V, I_D = 6A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	–	11	–	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	–	7.0	–	nC	
L_D	Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die.
L_S	Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.

Modified MOSFET symbol showing the internal device inductances.



Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	2.5	K/W	
R_{thCS}	Case-to-Sink	ALL	–	0.2	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	50	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ330 IRFJ331	–	–	4.5	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier.
		IRFJ332 IRFJ333	–	–	4.0	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFJ330 IRFJ331	–	–	18	A	
		IRFJ332 IRFJ333	–	–	15	A	
V_{SD}	Diode Forward Voltage ②	IRFJ330 IRFJ331	–	–	1.6	V	T_C = 25°C, I_S = 4.5A, V_{GS} = 0V
		IRFJ332 IRFJ333	–	–	1.5	V	T_C = 25°C, I_S = 4.0A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	–	600	–	ns	T_J = 150°C, I_F = 4.5A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	–	4.0	–	μC	T_J = 150°C, I_F = 4.5A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

①T_J = 25°C to 150°C. ②Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

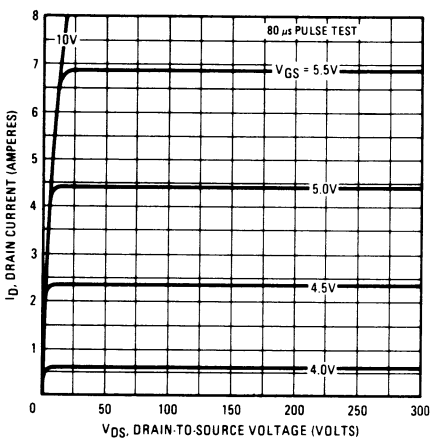


Fig. 1 – Typical Output Characteristics

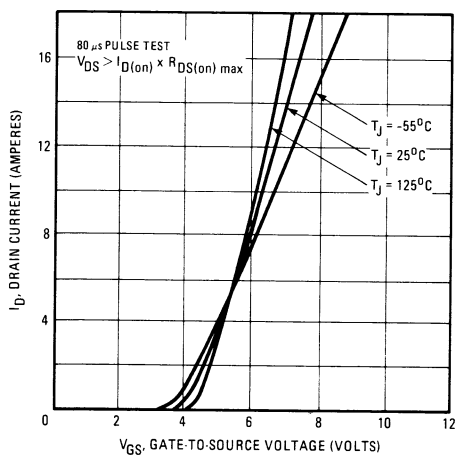


Fig. 2 – Typical Transfer Characteristics

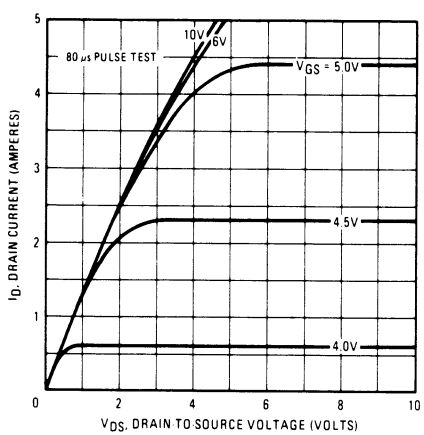


Fig. 3 – Typical Saturation Characteristics

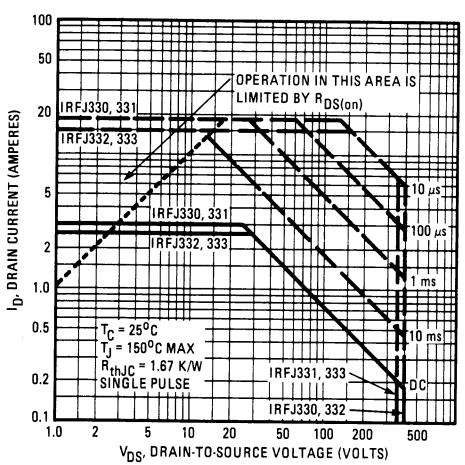


Fig. 4 – Maximum Safe Operating Area

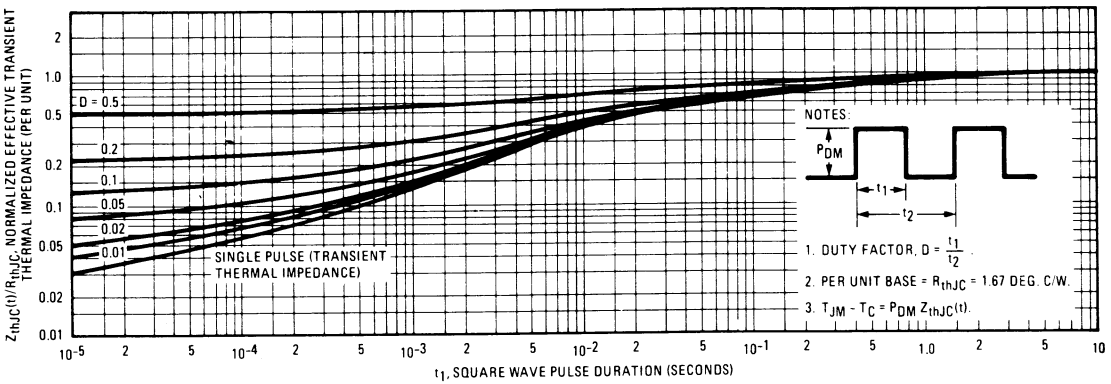


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

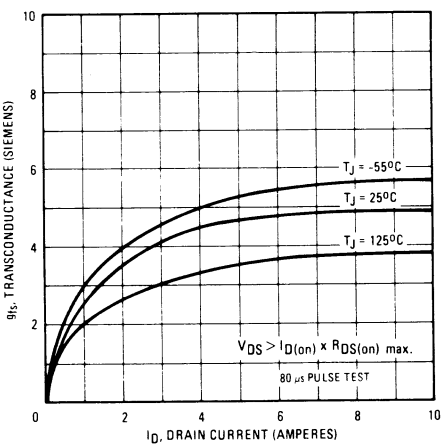


Fig. 6 — Typical Transconductance Vs. Drain Current

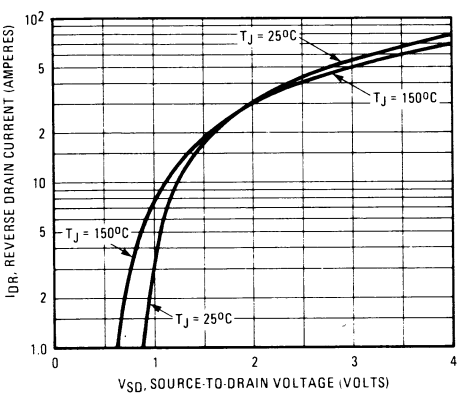


Fig. 7 — Typical Source-Drain Diode Forward Voltage

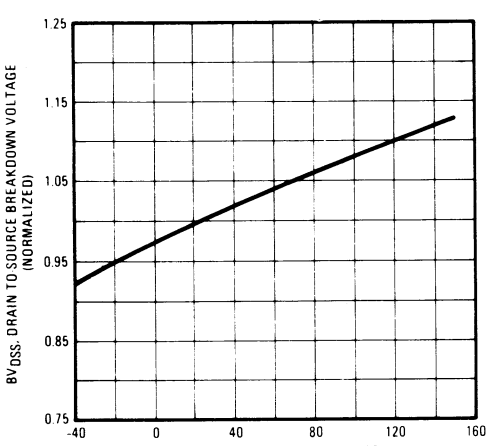


Fig. 8 — Breakdown Voltage Vs. Temperature

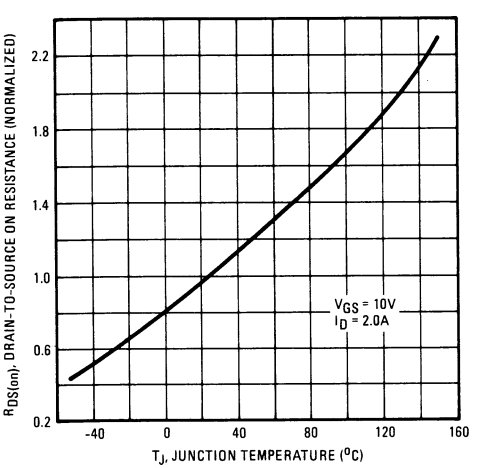


Fig. 9 — Normalized On-Resistance Vs. Temperature

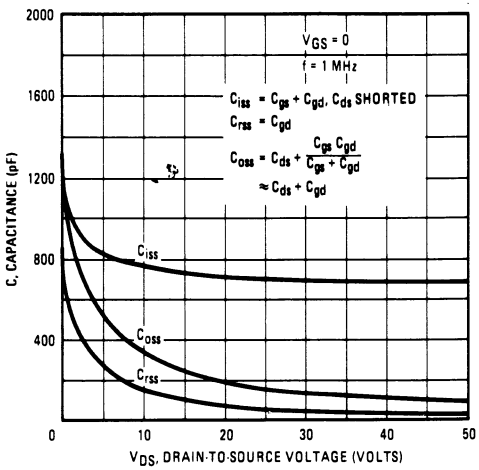


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

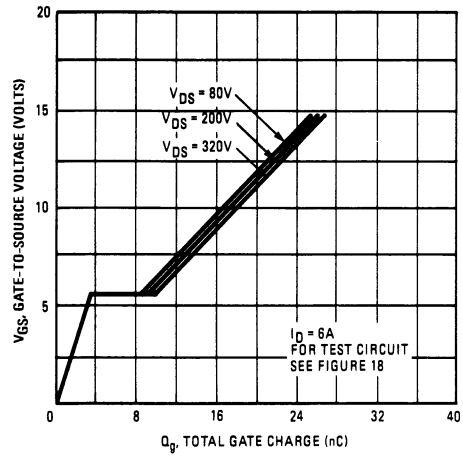


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

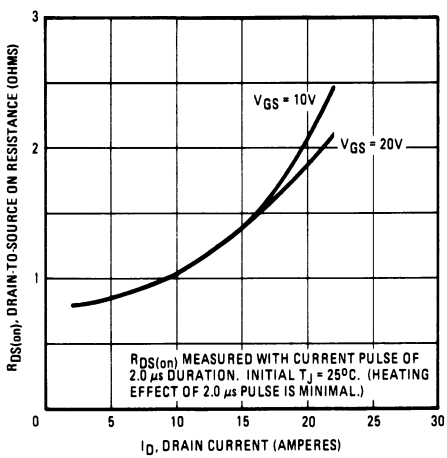


Fig. 12 — Typical On-Resistance Vs. Drain Current

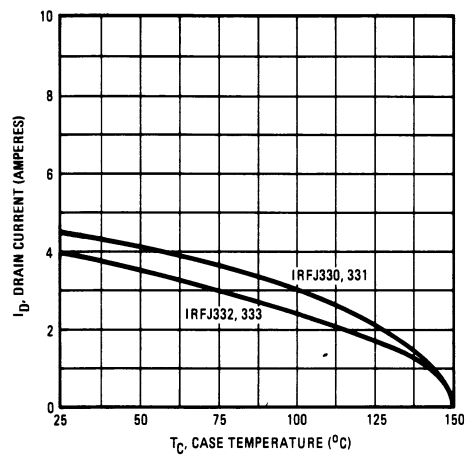


Fig. 13 — Maximum Drain Current Vs. Case Temperature

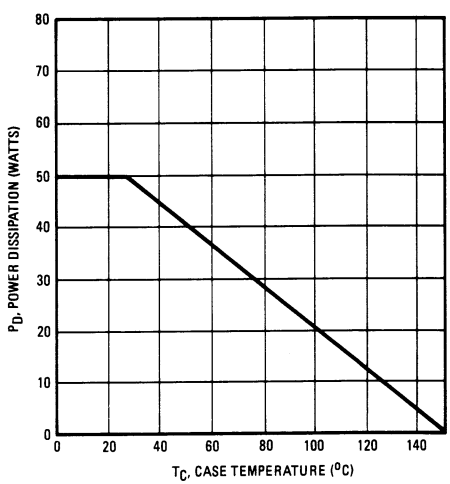


Fig. 14 — Power Vs. Temperature Derating Curve

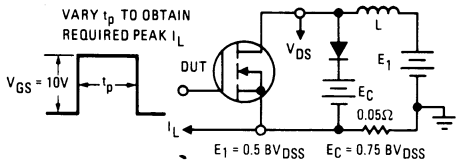


Fig. 15 – Clamped Inductive Test Circuit

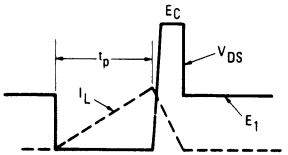


Fig. 16 – Clamped Inductive Waveforms

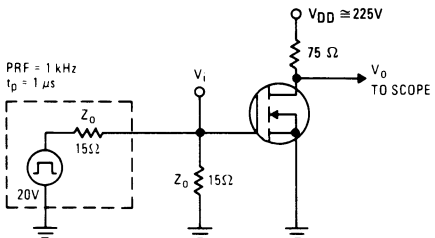


Fig. 17 – Switching Time Test Circuit

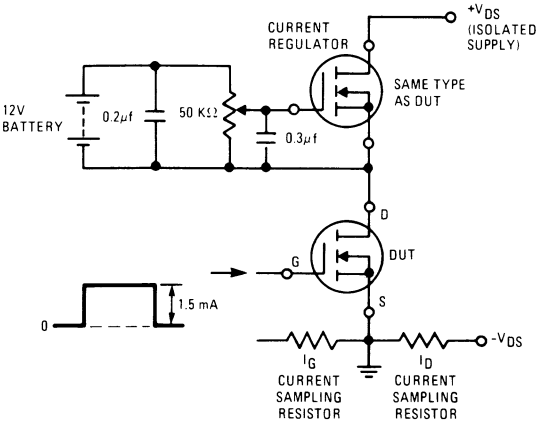


Fig. 18 – Gate Charge Test Circuit

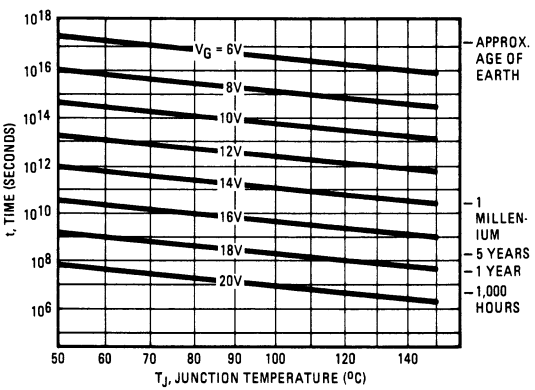


***Fig. 19 – Typical High Temperature Reverse Bias (HTRB) Failure Rate**

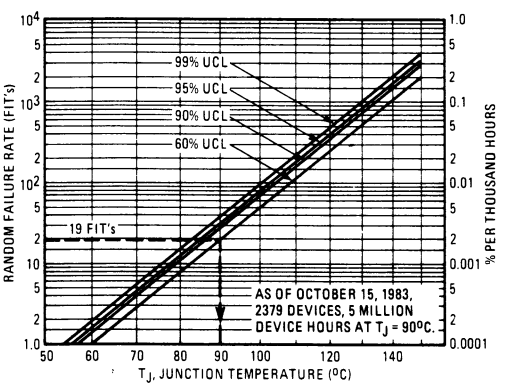


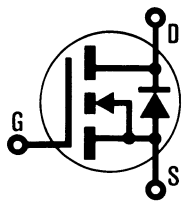
Fig. 20 – Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS IRFJ340 IRFJ341 IRFJ342 IRFJ343

N-CHANNEL POWER MOSFETs



400 Volt, 0.55 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, freedom from second breakdown, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

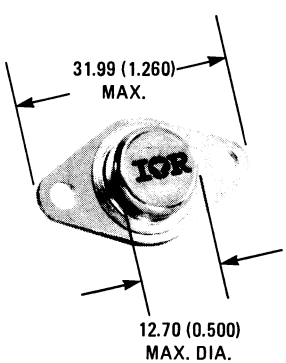
Features:

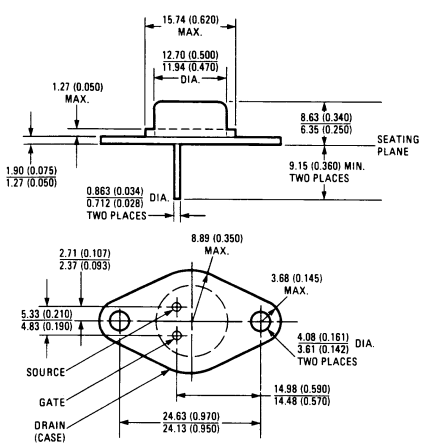
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ340	400V	0.55Ω	7.5A
IRFJ341	350V	0.55Ω	7.5A
IRFJ342	400V	0.80Ω	6.0A
IRFJ343	350V	0.80Ω	6.0A

CASE STYLE AND DIMENSIONS





Conforms to JEDEC Case Style TO-213AA (TO-66)
Dimensions in Millimeters and (Inches)

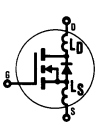
Absolute Maximum Ratings

Parameter		IRFJ340	IRFJ341	IRFJ342	IRFJ343	Units
V_{DS}	Drain - Source Voltage ①	400	350	400	350	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	400	350	400	350	V
I_D @ T_C = 25°C	Continuous Drain Current	7.5	7.5	6.0	6.0	A
I_D @ T_C = 100°C	Continuous Drain Current	5.0	5.0	4.0	4.0	A
I_{DM}	Pulsed Drain Current ③	30	30	25	25	A
V_{GS}	Gate - Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	70 (See Fig. 14)				W
	Linear Derating Factor	0.55 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH				A
		30	30	25	25	
T_J T_{stg}	Operating Junction and Storage Temperature Range	−55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFJ340 IRFJ342	400	–	–	V	V_{GS} = 0V
		IRFJ341 IRFJ343	350	–	–	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS}	Gate - Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V
I_{GSS}	Gate - Source Leakage Reverse	ALL	–	–	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFJ340 IRFJ341	7.5	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V
		IRFJ342 IRFJ343	6.0	–	–	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFJ340 IRFJ341	–	0.47	0.55	Ω	V_{GS} = 10V, I_D = 6.2A
		IRFJ342 IRFJ343	–	0.68	0.80	Ω	
g_{fs}	Forward Transconductance ②	ALL	4.0	7.5	–	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 6.2A
C_{iss}	Input Capacitance	ALL	–	1250	1600	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	–	300	450	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	–	80	150	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	17	35	ns	V_{DD} ≈ 175V, I_D = 6.2A, Z_o = 4.7Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	–	5.0	15	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	45	90	ns	
t_f	Fall Time	ALL	–	16	35	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	41	60	nC	V_{GS} = 10V, I_D = 9.5A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	–	18	–	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	–	23	–	nC	
L_D	Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die.
L_S	Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.

Modified MOSFET symbol showing the internal device inductances.



Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	1.8	K/W	
R_{thCS}	Case-to-Sink	ALL	–	0.2	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	50	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ340 IRFJ341	–	–	7.5	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRFJ342 IRFJ343	–	–	6.0	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFJ340 IRFJ341	–	–	30	A	
		IRFJ342 IRFJ343	–	–	25	A	
V_{SD}	Diode Forward Voltage ②	IRFJ340 IRFJ341	–	–	2.0	V	T_C = 25°C, I_S = 7.5, V_{GS} = 0V
		IRFJ342 IRFJ343	–	–	1.9	V	T_C = 25°C, I_S = 6.2A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	–	800	–	ns	T_J = 150°C, I_F = 7.5A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	–	5.7	–	μC	T_J = 150°C, I_F = 7.5A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

①T_J = 25°C to 150°C. ②Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

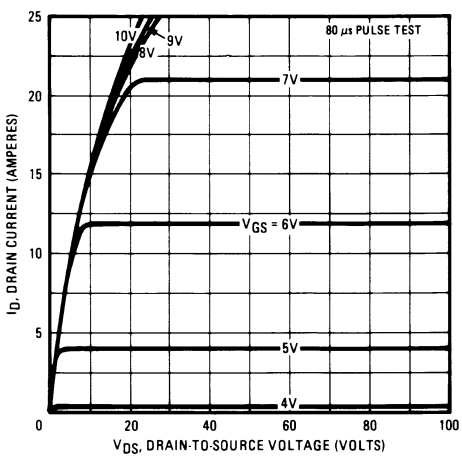


Fig. 1 – Typical Output Characteristics

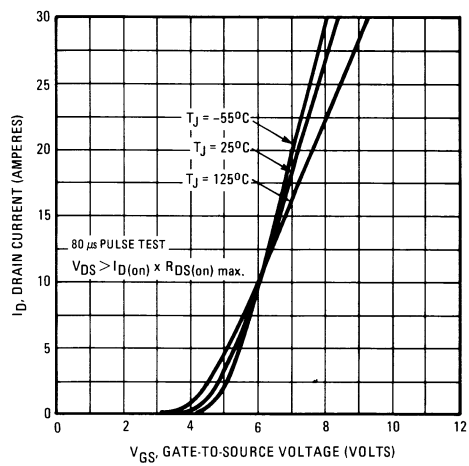


Fig. 2 – Typical Transfer Characteristics

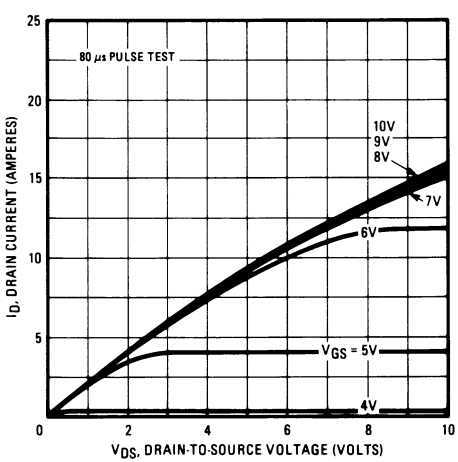


Fig. 3 – Typical Saturation Characteristics

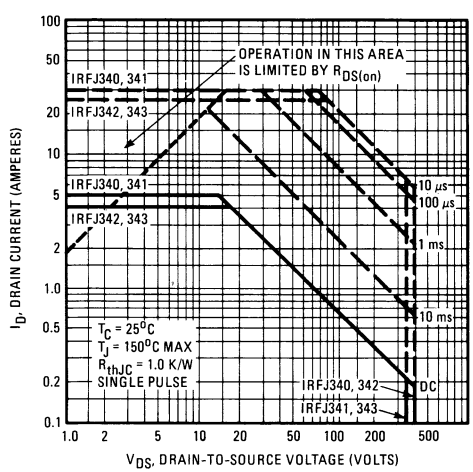


Fig. 4 – Maximum Safe Operating Area

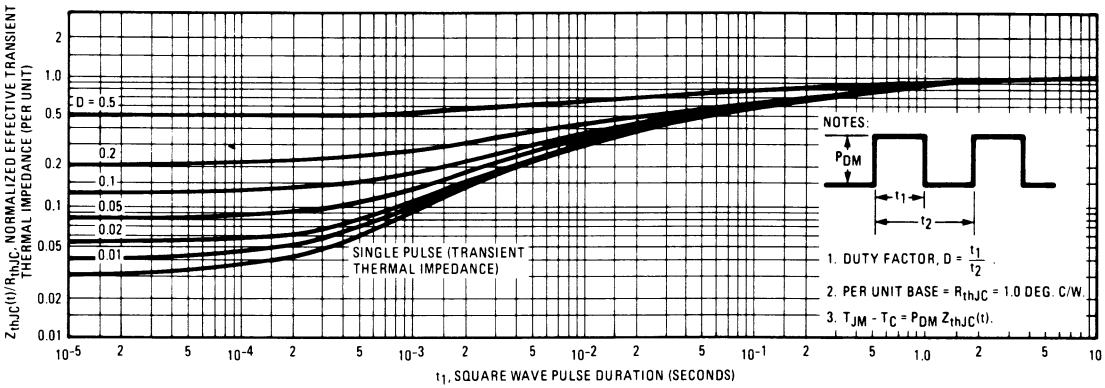


Fig. 5 – Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

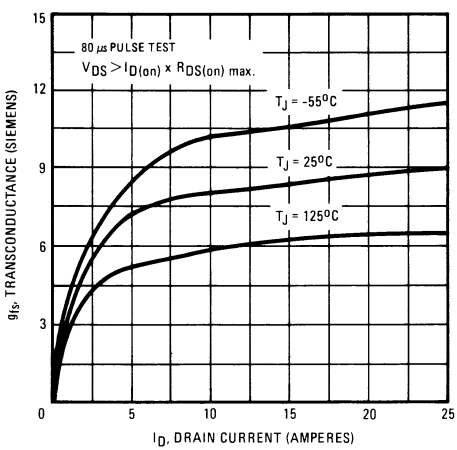


Fig. 6 – Typical Transconductance Vs. Drain Current

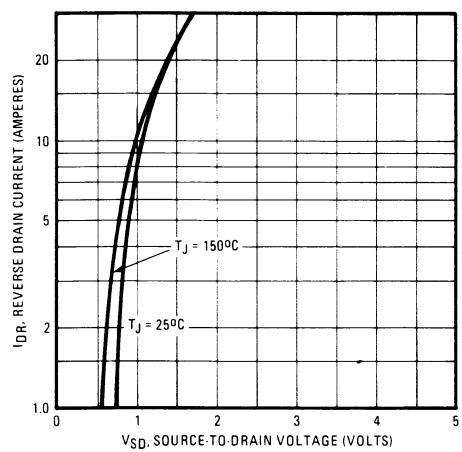


Fig. 7 – Typical Source-Drain Diode Forward Voltage

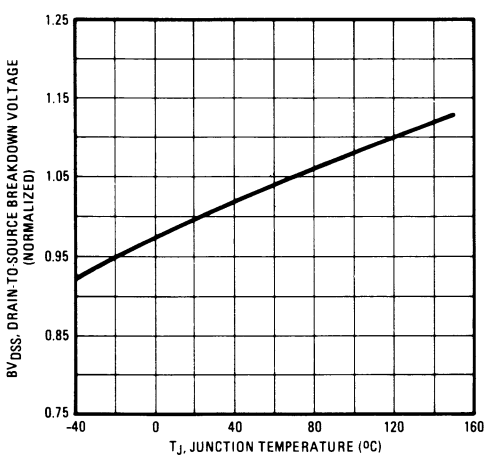


Fig. 8 – Breakdown Voltage Vs. Temperature

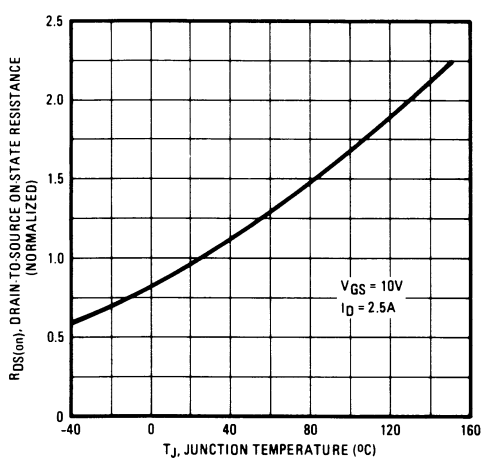


Fig. 9 – Normalized On-Resistance Vs. Temperature

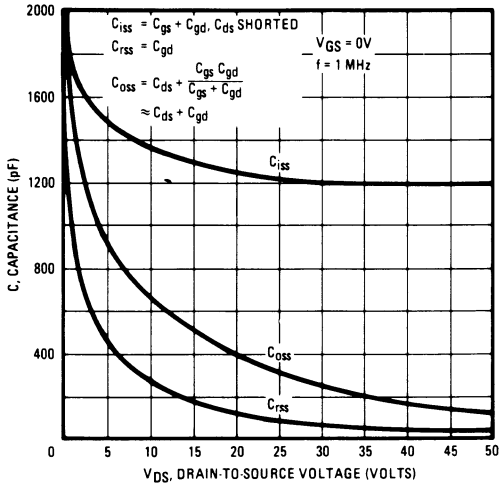


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

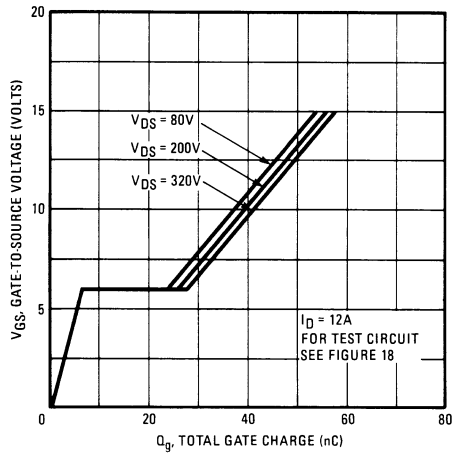


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

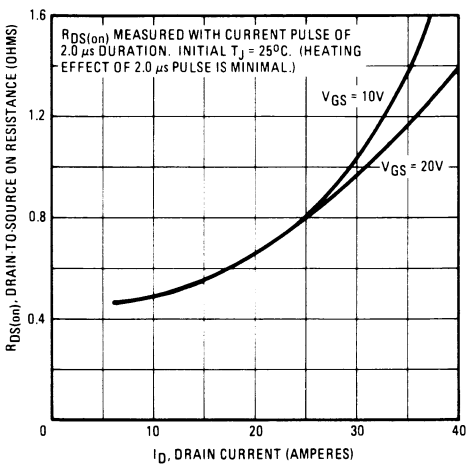


Fig. 12 — Typical On-Resistance Vs. Drain Current

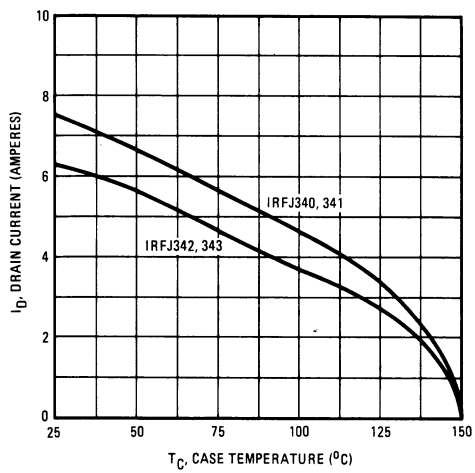


Fig. 13 — Maximum Drain Current Vs. Case Temperature

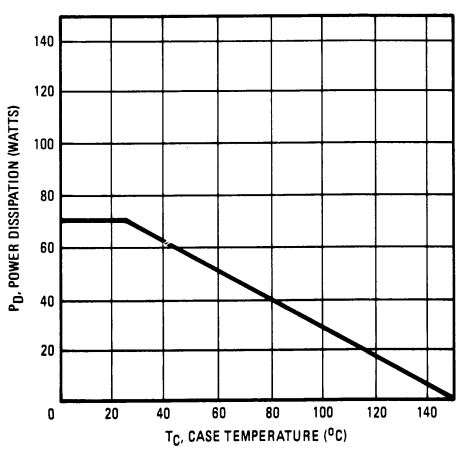


Fig. 14 — Power Vs. Temperature Derating Curve

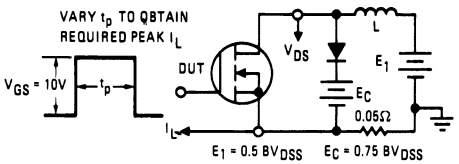


Fig. 15 – Clamped Inductive Test Circuit

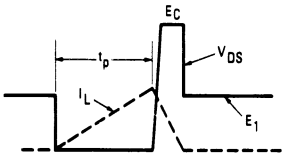


Fig. 16 – Clamped Inductive Waveforms

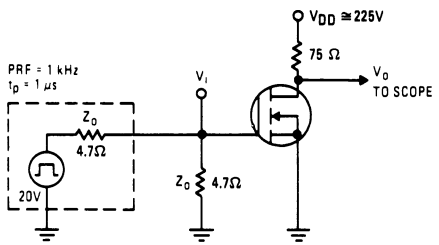


Fig. 17 – Switching Time Test Circuit

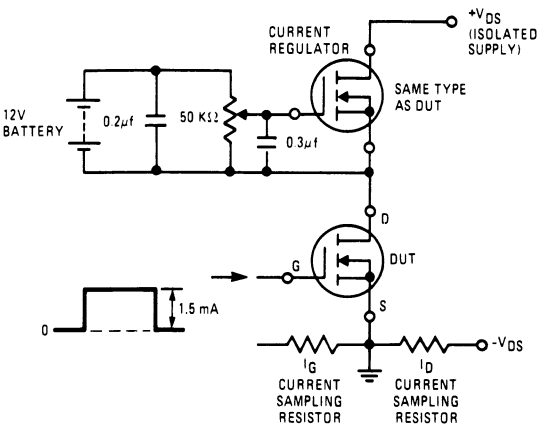


Fig. 18 – Gate Charge Test Circuit

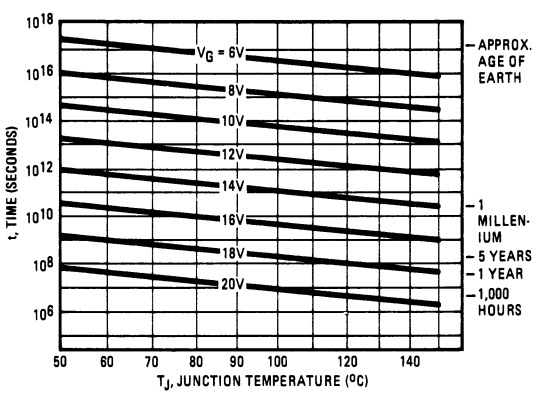


***Fig. 19 – Typical Time to Accumulated 1% Failure**

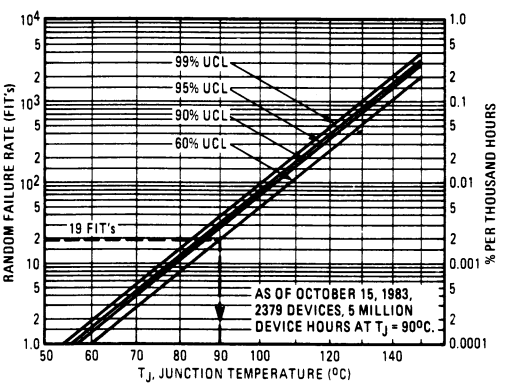


Fig. 20 – Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.